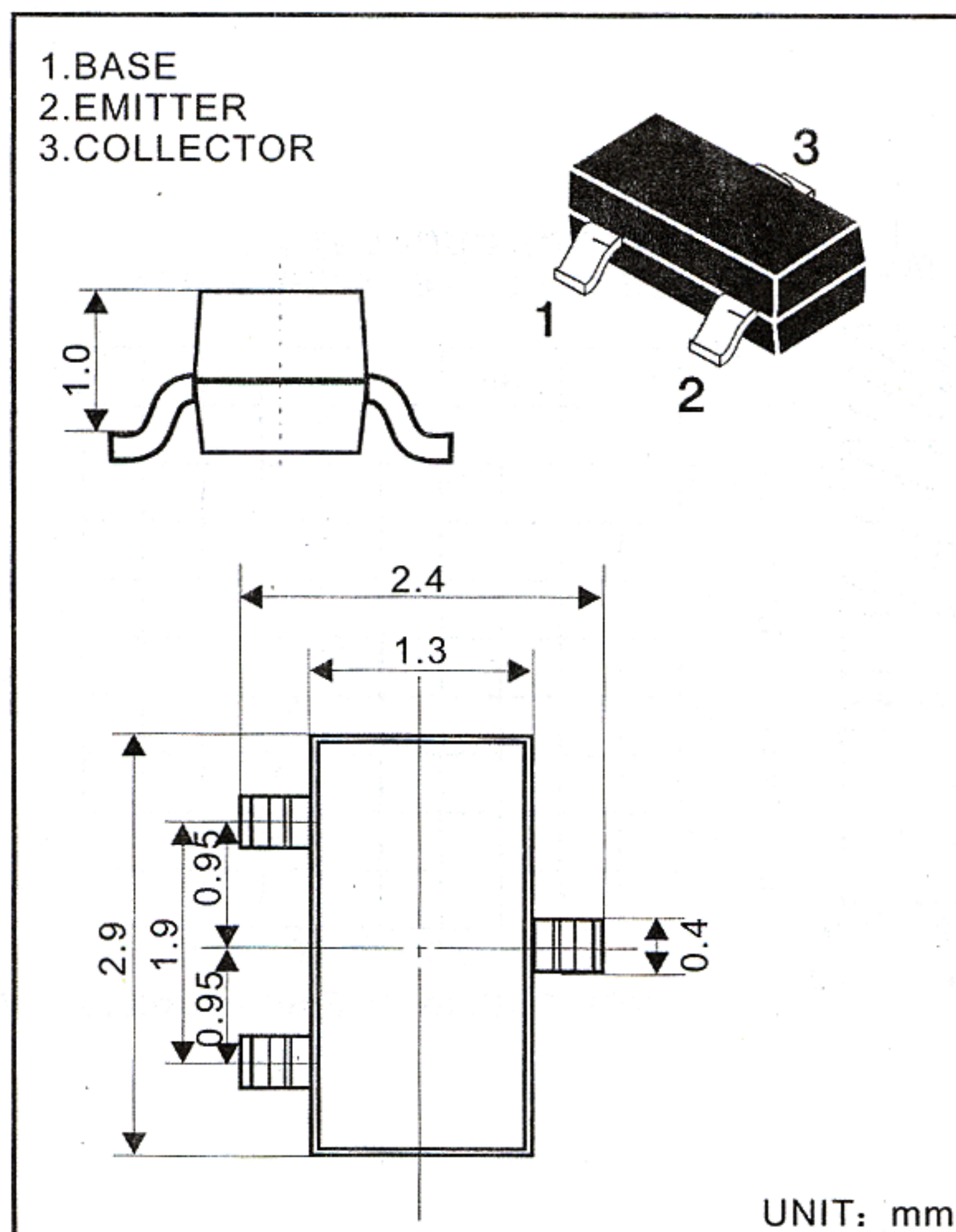


A733LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -60V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -5 \mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_C = -50 \mu A, I_B = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0mA$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	120	475	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100mA, I_B = -10mA$		-0.3	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -10mA, f = 30MHz$	100		MHz

CLASSIFICATION OF h_{FE}

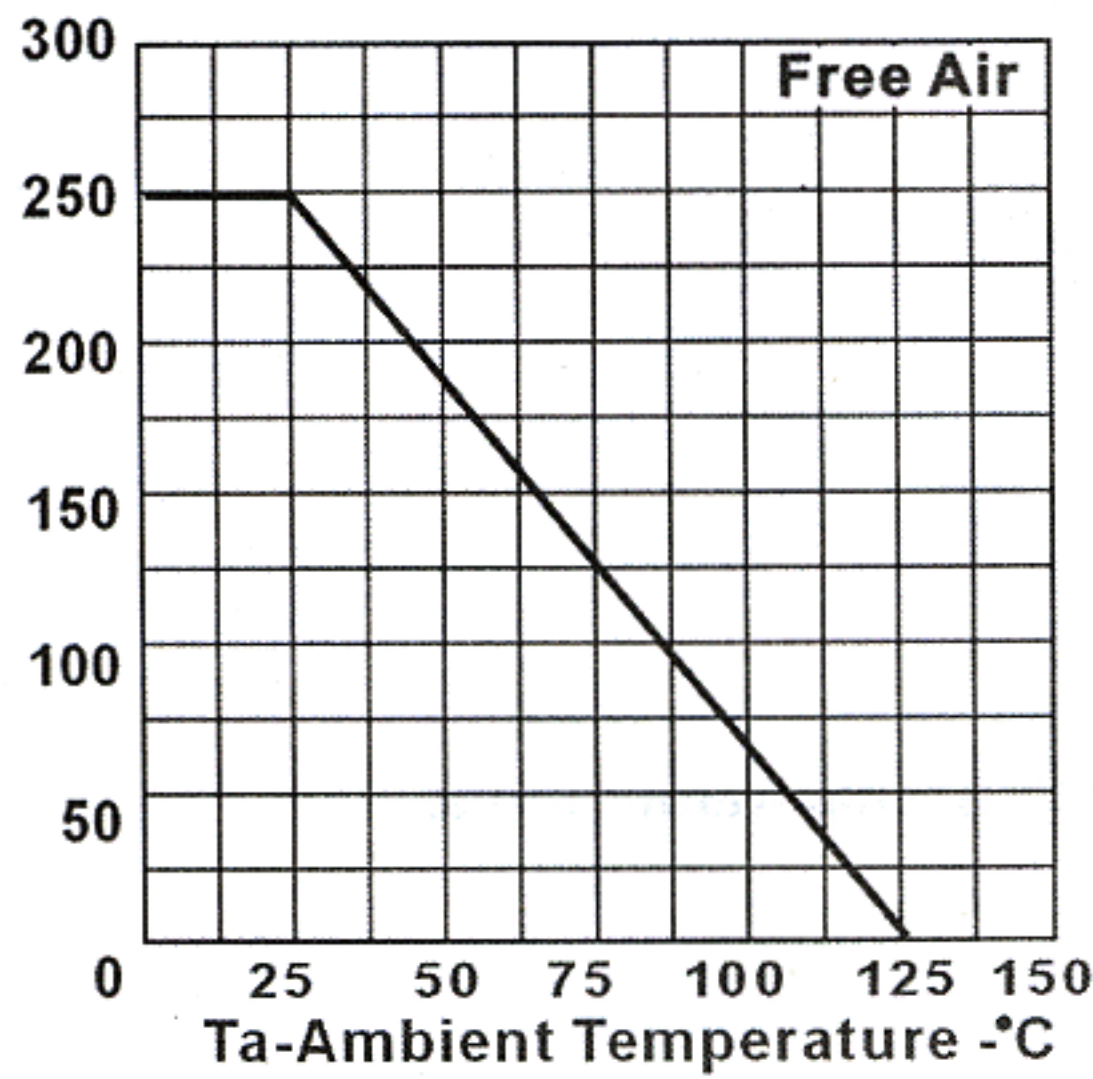
Rank	L	H
Range	120-200	200-475

DEVICE MARKING : A733LT1=CS

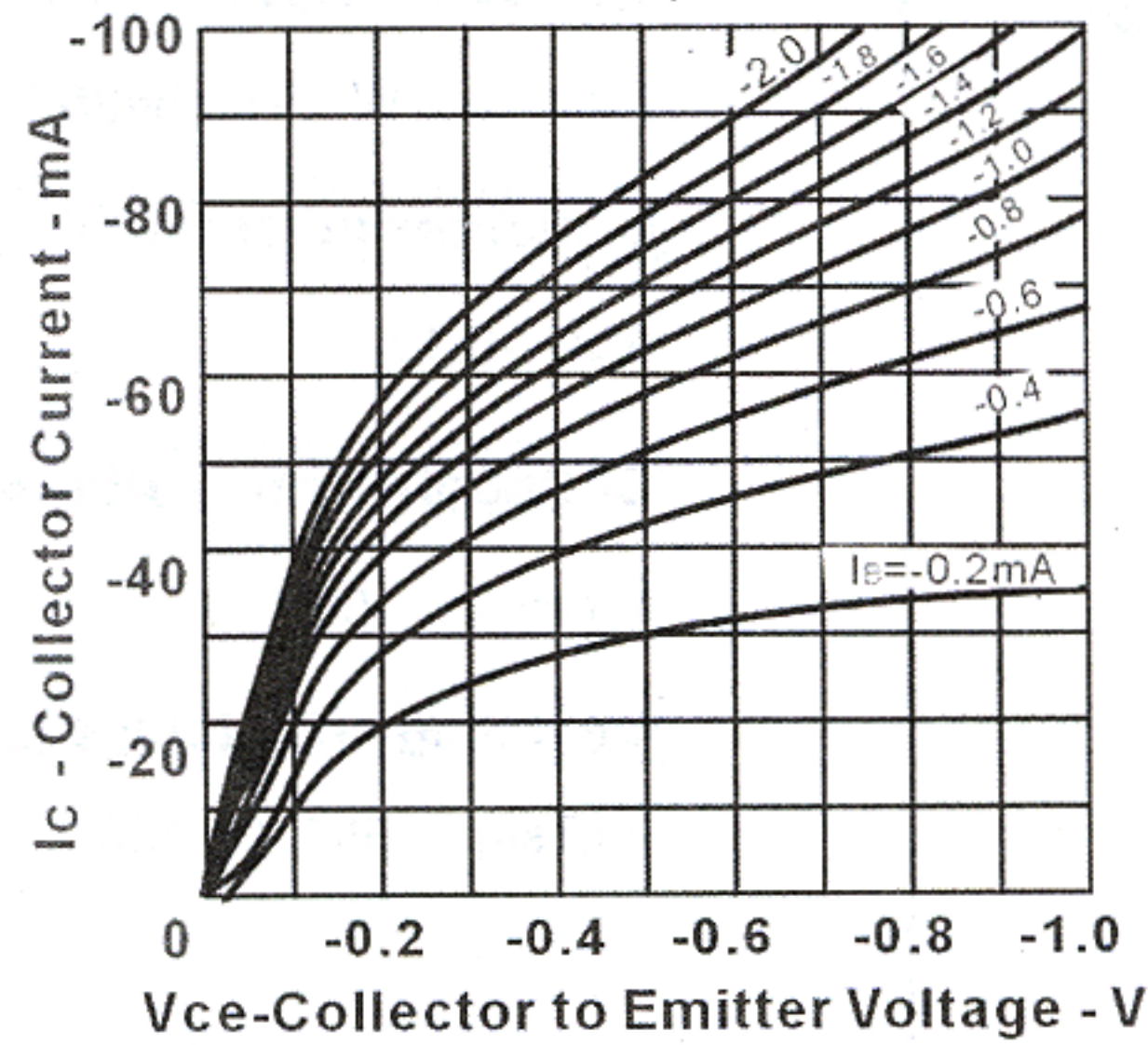
Typical Characteristics

A733LT1

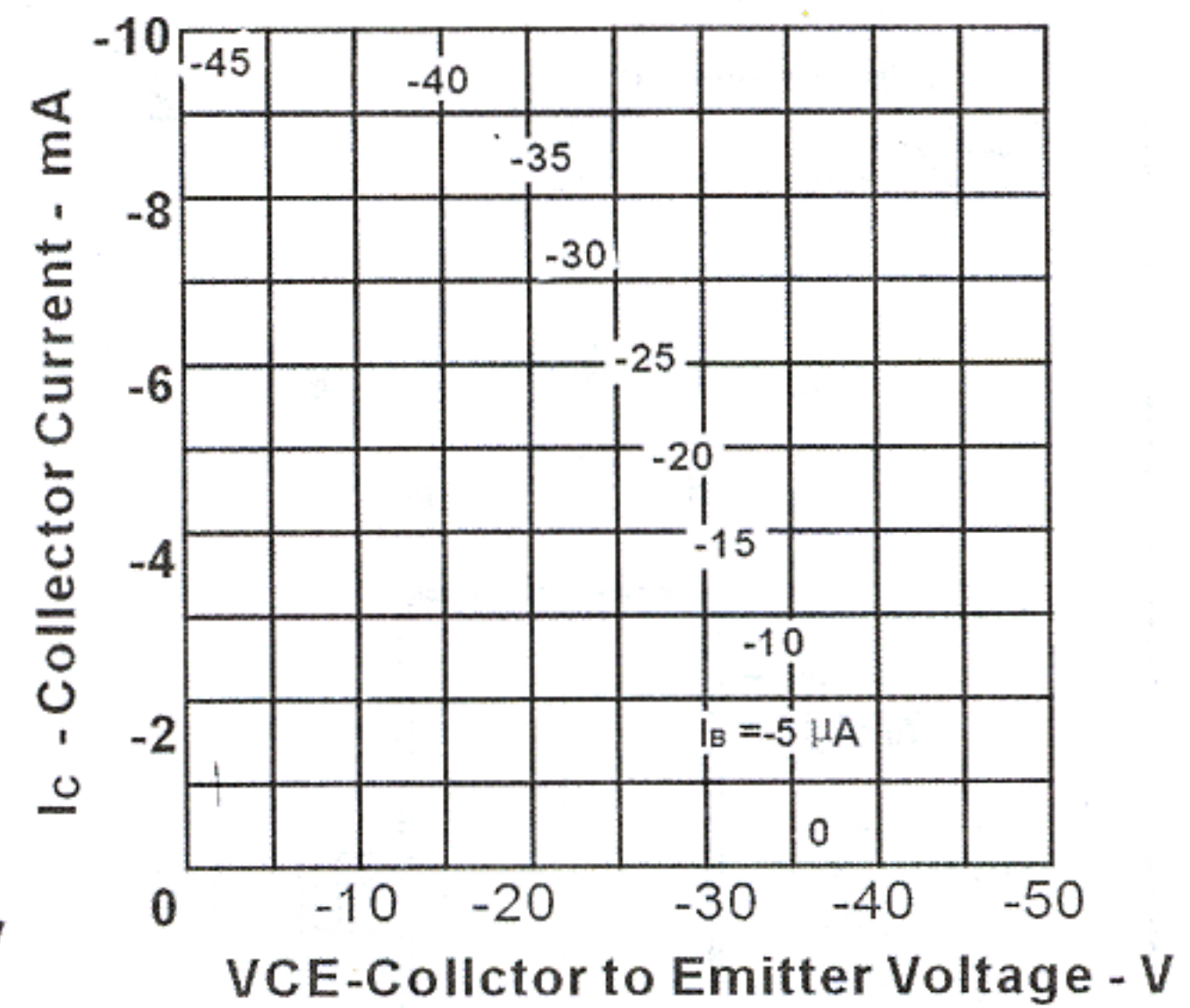
TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE



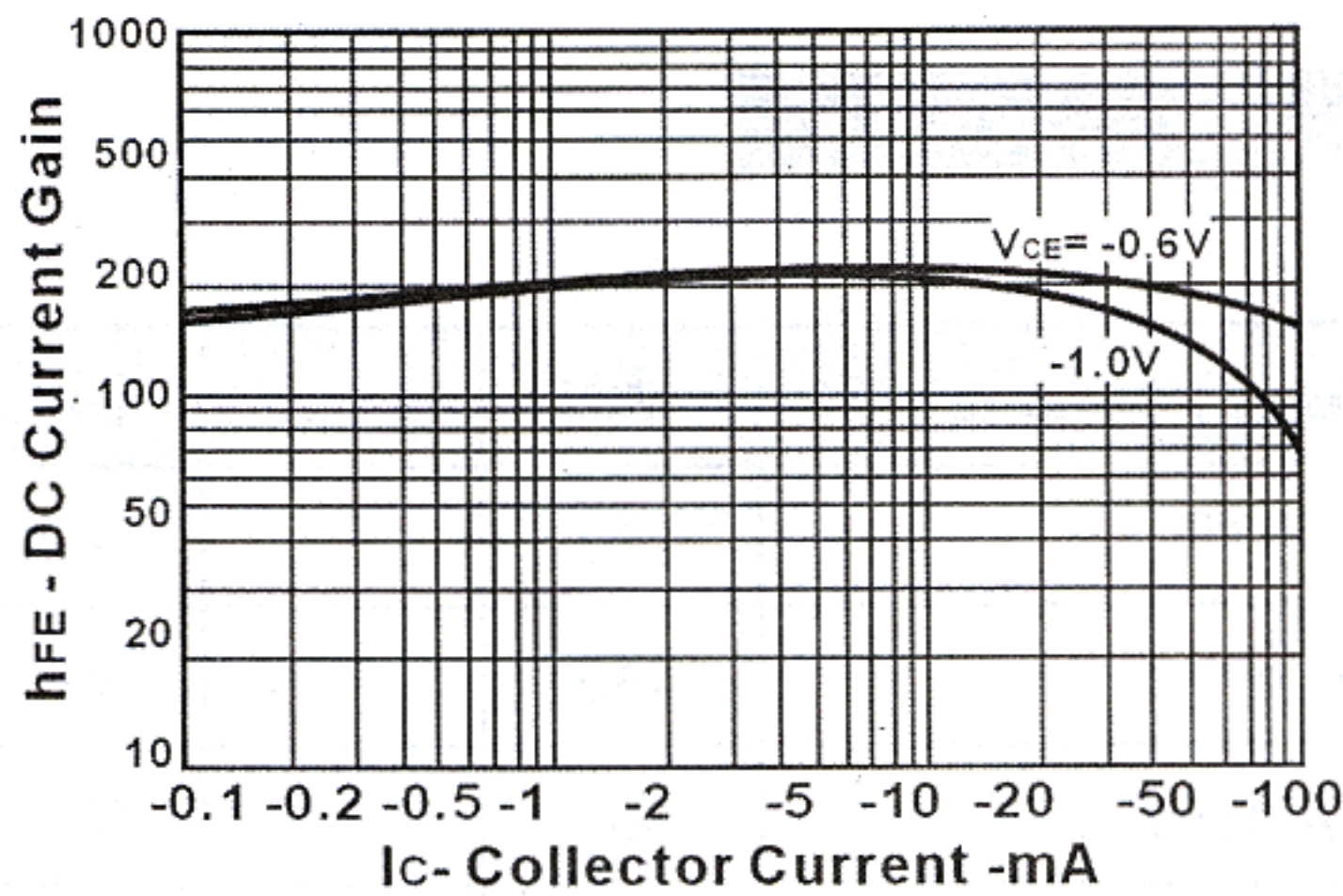
COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE



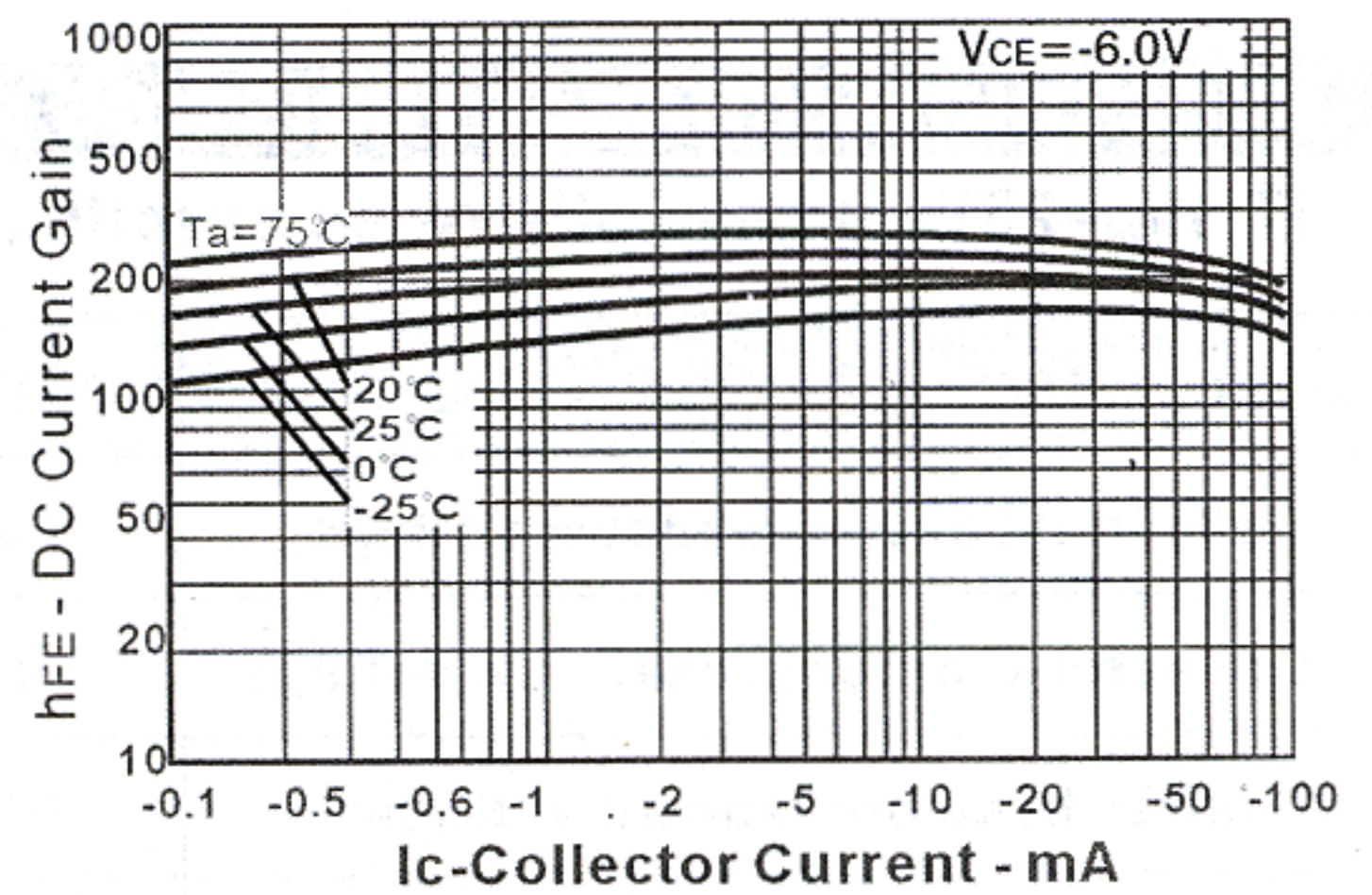
COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE



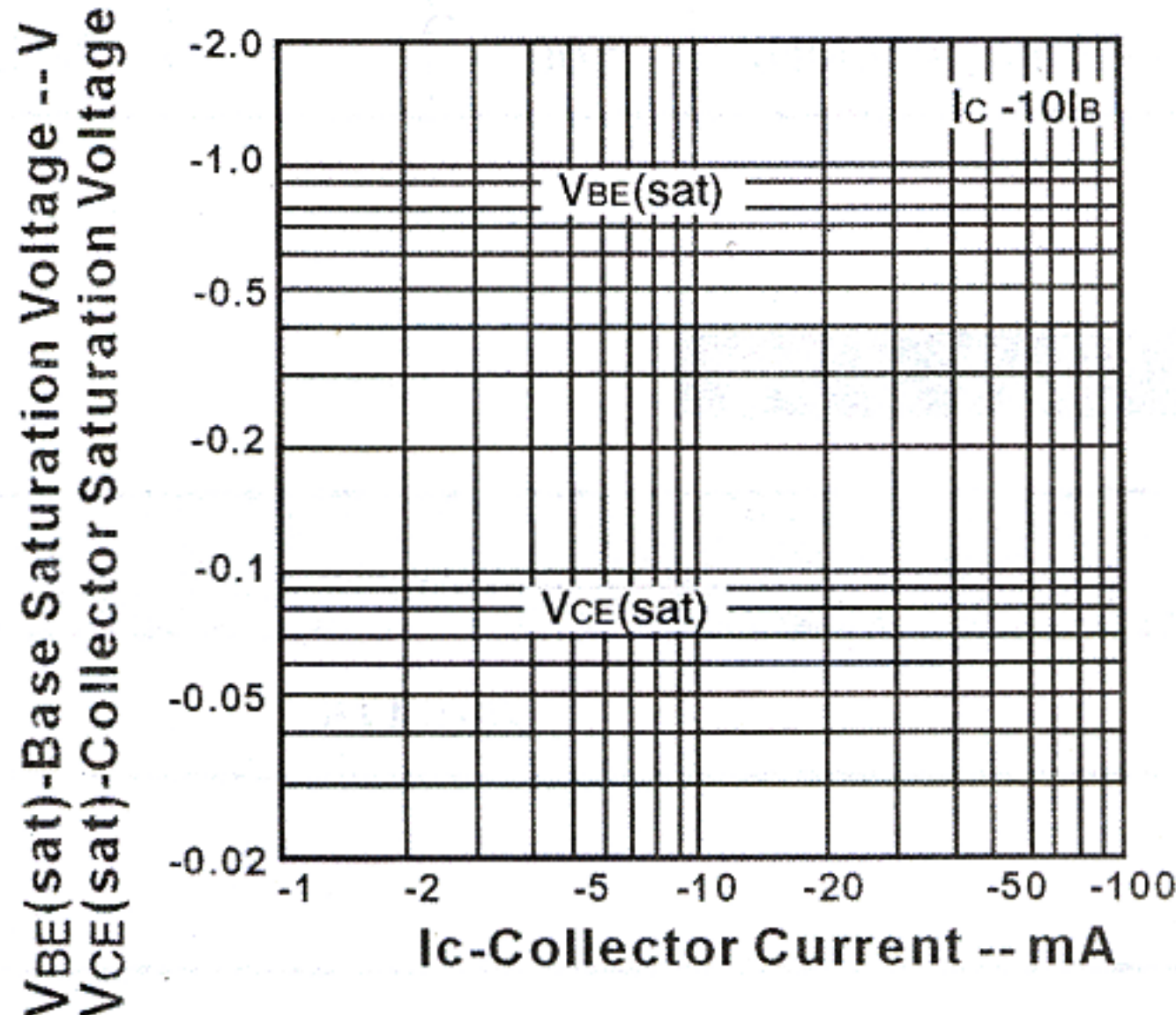
DC CURRENT GAIN vs.
COLLECTOR CURRENT



DC CURRENT GAIN vs.
COLLECTOR CURRENT



COLLECTOR AND BASE SATURATION
VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT
vs. EMITTER CURRENT

